

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	662910	(light near emitting near (diode or device or element)) or LED or (laser near diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:07
L2	16897	(single-crystal or (single near crystal\$4) or monocrystal\$4) near silicon near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:09
L3	208	II-VI near3 semiconductor near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:10
L4	1502	III-V near3 semiconductor near substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:11
L5	4037	(buffer near layer) with (GaN or AlGaIn or AlN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:13
L6	42543	clad\$4 near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:14
L7	247537	(silicon near nitride) or (aluminum near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:16
L8	26	I1 and I2 and I5 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:17
L9	10	I1 and I3 and I5 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:17
L10	58	I1 and I4 and I5 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 17:17